



PATENT  
8733.055.00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Youn Gyoung CHANG et al.

Application No.: 09/466,961

Group Art Unit: 2815

#5/A  
A-11-01

Examiner: Paul E. Brock III, Flowers

Filed: December 20, 1999

For: THIN FILM TRANSISTOR TYPE OPTICAL DETECTING SENSOR

AMENDMENT

Commissioner of Patents  
Washington, D.C. 20231

Sir:

In response to the Examiner's Office Action mailed on May 31, 2001, the following amendments and remarks are respectfully submitted.

RECEIVED  
SEP -6 2001  
TC 2800 MAIL ROOM

IN THE DRAWINGS

Please enter the legend --Related Art-- to Figures 1, 2, and 3.

Change the designation "29" to --21-- in Figure 2.

IN THE SPECIFICATION

On page 7, Paragraph beginning at Line 6, please amend as follows (Exhibit I is a marked up version of the amended Specification paragraph):

As shown in Fig. 4b, a first insulating layer 117, which is preferably one of the group consisting of aluminum oxide ( $Al_2O_x$ ), silicon oxide ( $SiO_x$ ) and tantalum oxide ( $TaO_x$ ), is deposited on the substrate 110 while covering the switch gate 115, the first capacitor electrode 113 and the sensor gate 111. An amorphous silicon layer and an  $n^+$  amorphous layer are

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